

The TAS0 is Low Profile version of the PRX TA20 high current disc pack SCR. It employs a Center-Fired amplifying gate structure. This amplifying gate design allows the SCR to be reliably operated at high di/dt and high dv/dt conditions in phase control applications.

FEATURES:

- Low On-State Voltage
- High di/dt Capability
- High dv/dt Capability
- Hermetic Ceramic Package
- Excellent Surge and I²t Ratings

APPLICATIONS:

- DC Power Supplies
- Motor Controls
- AC Soft-Starters

ORDERING INFORMATION

Select the complete 12 digit Part Number using the table below.
EXAMPLE: TAS0182603DH is a 1800V-2600A SCR with 200ma IGT and 12 inch gate and cathode potential leads.

PART	Voltage Rating $V_{DRM}-V_{RRM}$	Voltage Code	Current Rating I_{TAVG}	Current Code	Turn-Off T_q	Gate I_{GT}	Leads
TAS0	1800V	18	2600A	26	0	3	DH
	1600V	16					
	1400V	14			550us typ.	200ma	12"

Absolute Maximum Ratings

Characteristic	Symbol	Rating	Units
Repetitive Peak Voltage	$V_{DRM}-V_{RRM}$	1800	Volts
Non-repetitive Transient Peak Reverse Voltage	V_{RSM}	$V_{RRM} + 100$	Volts
Average On-State Current, $T_C=70^\circ\text{C}$	$I_{T(Avg.)}$	2635	A
RMS On-State Current, $T_C=70^\circ\text{C}$	$I_{T(RMS)}$	4139	A
Average On-State Current, $T_C=55^\circ\text{C}$	$I_{T(Avg.)}$	2775	A
RMS On-State Current, $T_C=55^\circ\text{C}$	$I_{T(RMS)}$	4359	A
Peak One Cycle Surge Current, 60Hz, $V_R=0V$	I_{TSM}	38,000	A
Peak One Cycle Surge Current, 50Hz, $V_R=0V$	I_{TSM}	35,826	A
Fuse Coordination I^2t , 60Hz	I^2t	6.02E+06	A^2s
Fuse Coordination I^2t , 50Hz	I^2t	6.42E+06	A^2s
Critical Rate-of-Rise of On-State Current	di/dt	100	A/us
Repetitive			
Critical Rate-of-Rise of On-State Current	di/dt	300	A/us
Non-Repetitive			
Peak Gate Power, 100us	P_{GM}	16	Watts
Average Gate Power	$P_{G(avg)}$	5	Watts
Operating Temperature	T_j	-40 to+125	$^\circ\text{C}$
Storage Temperature	$T_{Stg.}$	-50 to+150	$^\circ\text{C}$
Approximate Weight		2.1	lb
		0.95	Kg
Mounting Force		9000 - 11000	lbs
		40.0 - 48.9	Knewtons

Information presented is based upon limited testing or projected capabilities. This information is subject to change without notice. The manufacturer makes no claim as to suitability for use, reliability, capability or future availability of this product.



TASO_2603DH

Phase Control Thyristor

Powerex, Inc., 173 Pavilion Ln, Youngwood, Pa 15697-1800 (724)925-7272 //www.pwr.com

2600 Amperes 1800 Volts

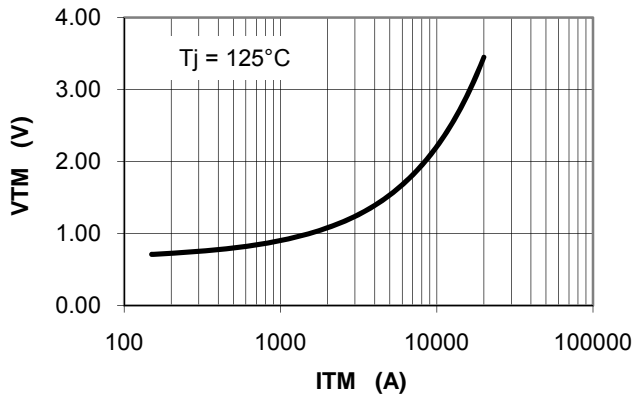
Electrical Characteristics, Tj=25°C unless otherwise specified

Characteristic	Symbol	Test Conditions	Rating			Units
			min	typ	max	
Repetitive Peak Forward Leakage Current	I_{DRM}	Tj=125°C, V_{DRM} =Rated			150	ma
Repetitive Peak Reverse Leakage Current	I_{RRM}	Tj=125°C, V_{RRM} =Rated			150	ma
Peak On-State Voltage	V_{TM}	Tj=25°C, I_{TM} =3000A			1.35	V
V_{TM} Model, Low Level	V_0	Tj=125°C			0.735	V
$V_{TM} = V_0 + r \cdot I_{TM}$	r	15% $I_{TM} - \pi \cdot I_{TM}$			0.163	mΩ
V_{TM} Model, High Level	V_0	Tj=125°C			0.982	V
$V_{TM} = V_0 + r \cdot I_{TM}$	r	$\pi \cdot I_{TM} - I_{TSM}$			0.123	mΩ
V_{TM} Model, 4-Term	A	Tj=125°C			0.665	
$V_{TM} = A + B \cdot \ln(I_{TM}) +$	B	15% $I_{TM} - I_{TSM}$			-0.010	
$C \cdot (I_{TM}) + D \cdot (I_{TM})^{1/2}$	C				9.75E-05	
	D				6.58E-03	
Turn-On Delay Time	t_d	$V_D = 0.5 \cdot V_{DRM}$ Gate Drive: 40V - 20Ω			2.5	us
Turn-Off Time	tq	Tj=125°C dv/dt = 20V/us to 80% V_{DRM}			550	us
dv/dt _(crit)	dv/dt	Tj=125°C Exp. Waveform $V_D = 80\%$ Rated			800	V/us
Gate Trigger Current	I_{GT}	Tj=25°C $V_D = 12V$	30	125	200	ma
Gate Trigger Voltage	V_{GT}		0.8	2.0	4.5	V
Peak Reverse Gate Voltage	V_{GRM}				5	V

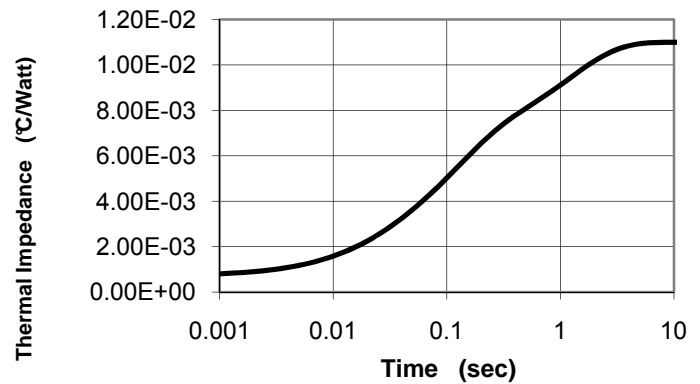
Thermal Characteristics

Characteristic	Symbol	Test Conditions	Rating			Units	
			min	typ	max		
Thermal Resistance							
Junction to Case	$R\theta_{jc}$	Double side cooled		0.01	0.011	°C/Watt	
Case to Sink	$R\theta_{cs}$	Double side cooled		0.003	0.005	°C/Watt	
Thermal Impedance Model							
$Z\theta_{jc}(t) = \Sigma(A(N) \cdot (1 - \exp(-t/\text{Tau}(N))))$		Double side cooled					
	where:		N =	1	2	3	4
			A(N) =	7.00E-04	1.00E-03	5.00E-03	4.30E-03
			Tau(N) =	8.00E-05	1.90E-02	1.10E-01	1.21E+00

Maximum On-State Voltage Drop

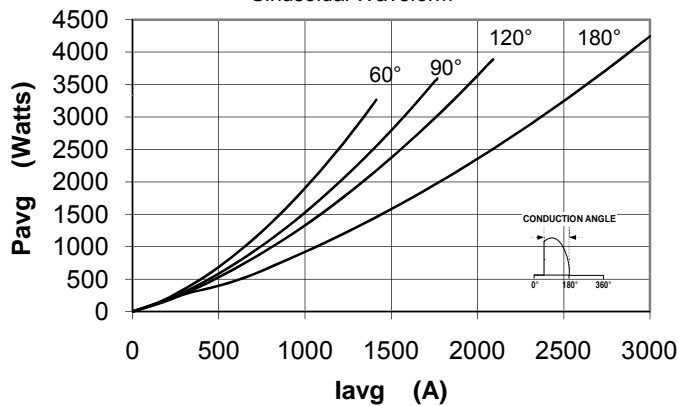


MAXIMUM TRANSIENT THERMAL IMPEDANCE



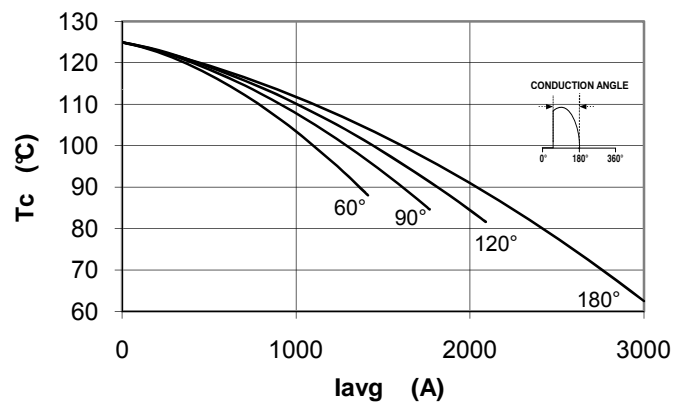
Maximum On-State Power Dissipation

Sinusoidal Waveform



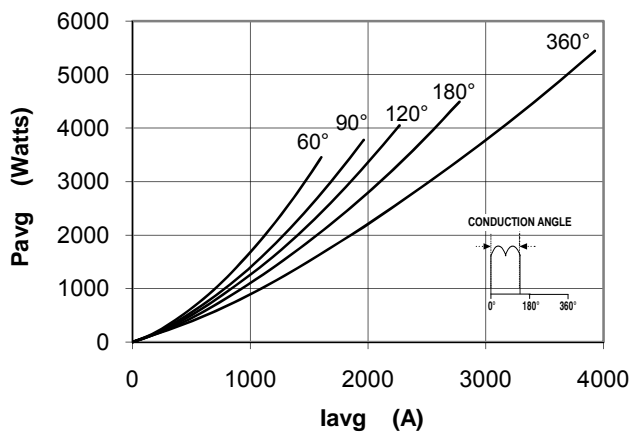
Maximum Allowable Case Temperature

Sinusoidal Waveform



Maximum On-State Power Dissipation

Square Waveform



Maximum Allowable Case Temperature

Square Waveform

